

L Number	Hits	Search Text	DB	Time stamp
2	79	438/\$.ccls. and (HVN MOS (high adj voltage HV) adj NMOS) and (HVPMOS (high adj voltage HV) adj PMOS)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 14:51
1	121	257/\$.ccls. and (HVN MOS (high adj voltage HV) adj NMOS) and (HVPMOS (high adj voltage HV) adj PMOS)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 14:49
4	179	(HVN MOS (high adj voltage HV) adj NMOS) and (HVPMOS (high adj voltage HV) adj PMOS)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 16:49
6	1881	(257/369).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 15:44
9	77	((257/344).CCLS.) and CMOS ) and (n N) adj well and (P p) adj well	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 16:06
-	148	(438/224).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 10:47
-	165	(257/491).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/11 14:37
-	593	(257/339).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 09:54
-	91	((257/339).CCLS.) and CMOS	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 09:54
-	32	((257/339).CCLS.) and p adj well and n adj well	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 09:55
-	109	(257/168).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 10:00
-	1033	(257/344).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 10:47
-	391	((257/344).CCLS.) and CMOS	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 16:06
-	436	(257/357).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 11:01
-	15	((257/357).CCLS.) and (n N) adj2 (deep buried)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 11:02
-	885	(257/370).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 11:03
-	28	((257/357).CCLS.) and (n N) near2 (deep buried)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 11:53

-	87	((257/369).CCLS.) and (n N) near2 (deep buried)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 11:25
-	166	((257/370).CCLS.) and (n N) near2 (deep buried)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 11:35
-	120	((257/370).CCLS.) and (n N) adj2 buried	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 13:23
-	1	09/973390	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 11:53
-	629	257/\$.ccls. and (HVMOS HVPMOS (high adj voltage HV) adj (NMOS PMOS MOS))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 13:09
-	32	257/\$.ccls. and (HVMOS HVPMOS)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 12:08
-	75	257/\$.ccls. and (HVMOS HVPMOS HV adj (NMOS PMOS))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 13:07
-	613	(257/371).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 13:09
-	773	(257/409).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 13:09
-	132	((257/409).CCLS.) and CMOS	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 13:09
-	44	((257/409).CCLS.) and (HVMOS HVPMOS (high adj voltage HV) adj (NMOS PMOS MOS))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 13:10
-	61	((257/371).CCLS.) and (n N) near2 buried	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 13:19
-	183	((257/370).CCLS.) and (n N) adj well and (p P) adj well	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/12 13:23